



## **B-Mount**

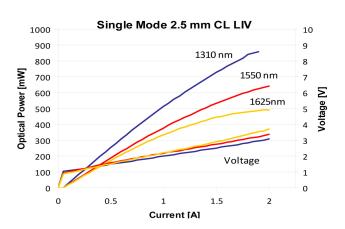
High Power Single-Mode and Multi-Mode SemiNex Lasers 12xx to 19xx nm Custom Wavelengths Available Lensed Options Available

- ApplicationsOEM MedicalDPSS pump source
- Lidar .
- Military / Aerospace
- Features .
- Cost effective High Output Power .
- . High Dynamic Range
- High EfficiencyStandard Low Cost Package



SemiNex delivers the highest available power at infrared wavelengths between 12xxnm and 16xxnm as well 19xxnm wavelengths between 12xxnm and 16xxnm as well 19xxnm to 24xxnm. When necessary we will further optimize the design of our InP or GaSb laser chips to meet our customers' specific optical and electrical performance needs. Diodes, bars and packages are tested to meet customer and market performance demands. Typical results and packaging options are shown. Contact SemiNex for additional details or to discuss your specific requirements.





11/30/23, 4:15 PM

PI Sheet





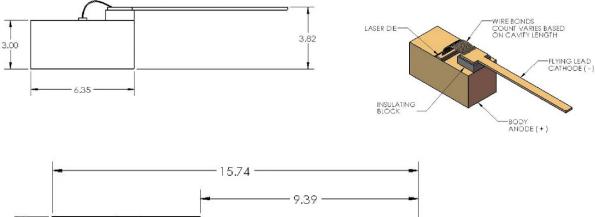


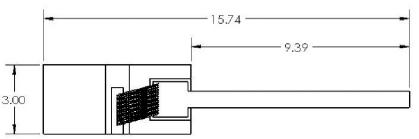
	Symbol	B-124	Units
Optical			
Wavelength	λ <sub>c</sub>	1660	nm (±20)
Output Power (CW)	P°	0.45	watts (±10%)
Chip Cavity Length	CL	2500	μm
Emitter Width	W	5	μm
Emitter Height	н	1	μm
Spectral Width	δλ	15	nm 3dB
Slope Efficiency	η°	0.25	W/A
Fast Axis Div.*	Θ_perp	30	deg FWHM
Slow Axis Div.	O_parallel	10	deg FWHM
Electrical			
Power Conversion Eff.	η	14	%
Threshold Current	I <sub>th</sub>	0.05	A
Operating Current	I <sub>op</sub>	1.4	A
Operating Voltage	V <sub>op</sub>	2.2	V
Mechanical			
Weight		0.5	g
Operating Temp.**		-40 to 60	°C
Storage Temp.		-40 to 80	°C
Operating Voltage Min.		2.1	V
Operating Voltage Max.		2.2	V

**B-Mount** 

Specified values are rated at a constant heat sink temperature of 20°C. \*\*Specified operating conditions are based on 20C heat sink temperature. High temperature operation will reduce performance and MTTF. Unless otherwise indicated all values are nominal. \*Fast Axis Divergence can be changed with lens option.







All statements, technical information and recommendations related to the product herein are based upon information believed to be reliable or accurate. The accuracy or completeness herein is not guaranteed, and no responsibility is assumed for any inaccuracies. The user assumes all risks and liability whatsoever in connection with the use of a product or its application. SemiNex Corporation reserves the right to change at any time without notice the design, specification, deduction, fit or form of its described herein, including withdrawal at any time of a product for each erein. Users are encouraged to visit www.seminex.com for the latest data. SemiNex Corporation makes no representations that the products herein are free from any intellectual property claims of others. Please contact SemiNex for more information.  $\diamondsuit$  2016 SemiNex Corporation

SemiNex Corporation • 153 Andover St • Danvers, MA 01923 • 978-326-7700 • Email: info@seminex.com • www.seminex.com

Date Created: Nov 30 2023 10:07PM UTC

DANGER LE / INVISIBLE LASER RADIATION ID DIRECT EXPOSURE TO BEAU CLASS IIIb and IV LASER PRODUCTS This product complies with 2/CFR1040 as applicab Laser aperture is on the test station. Later radiation from this product is considered an acute hazard to t skin and eyes.